



PATENT  
Attorney Docket No. ASC-057C1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S): Hammond *et al.* CONF. NO.: 2980  
SERIAL NO.: 10/797,231 ART UNIT: 2812  
FILING DATE: March 10, 2004 EXAMINER: Ghyka, Alexander G.  
TITLE: Method of Selective Removal of SiGe Alloys

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. § 1.97 and 1.98, Applicants hereby make of record the information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application.

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

- ☐ (1) within three (3) months of the **filing date** of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the **date of entry of the national stage** as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the **first Office action** on the merits, or before the mailing of a **first Office action** after the filing of a request for continued examination under 37 C.F.R. 1.114; or
- ☒ (2) after the period defined in (1) but before the mailing date of a **final action** or a **notice of allowance** under 37 C.F.R. 1.311, and
- ☐ the requisite Statement is below, **OR**
- ☒ the requisite fee under 37 C.F.R. 1.17(p), namely **\$180.00**, is included herein, or
- ☐ (3) after the mailing date of a **final action** or **notice of allowance** but before the payment of the **issue fee**, **AND**

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- ☐ the requisite Statement is below, **AND**
- ☐ the requisite petition fee under 37 C.F.R. 1.17(p), namely **\$180.00** is included herein.

Pursuant to MPEP section 2001.06(c), applicants hereby apprise the U.S. Patent and Trademark Office that the parent of the instant application is currently the subject of a litigation captioned AmberWave Systems Corporation v. Intel Corporation, Civil Action No. 05-837-KAJ.


It is respectfully requested that the information contained herein be made of record in this application.

Respectfully submitted,

Date: August 16, 2006  
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LIBC/2825963.1

  
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FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-057C1					
SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Hammond <i>et al.</i>					
				SERIAL NO.: 10/797,231					
				FILING DATE: March 10, 2004 GROUP: 2812					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A67	5,417,180	5/23/1995	Nakamura					
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
	C74	Chang, G.K., <i>et al.</i> , "Selective Etching of SiGe on SiGe/Se Heterostructures," J. ELECTROCHEM. SOC. (1999) 138(1):202-04.							
	C75	Ismail, K., "Si/SiGe High-Speed Field Effect Transistors," IEEE IEDM TECH. DIG. (1995) 509-12.							
	C76	LeGoues, F.K. <i>et al.</i> , "Oxidation studies of SiGe," J. APPL. PHYS. (1989) 65(4): 1724-28.							
	C77	Rhee, S.S., <i>et al.</i> , "SiGe Resonant Tunneling Hot Carrier Transistor," IEEE IEDM TECH. DIG. (1999) 651-54.							
	C78	Wolf, S., SILICON PROCESSING FOR THE VLSI ERA: VOL.2-PROCESS INTEGRATION (1990) Lattice Press, 66-83.							
EXAMINER					DATE CONSIDERED				

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